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FDG330P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

Applications

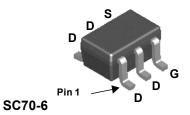
- · Battery management
- · Load switch

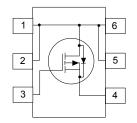
Features

• –2 A, –12 V. $R_{DS(ON)} = 110 \ m\Omega \ @ \ V_{GS} = -4.5 \ V$ $R_{DS(ON)} = 150 \ m\Omega \ @ \ V_{GS} = -2.5 \ V$

 $R_{DS(ON)}$ = 215 m Ω @ V_{GS} = -1.8 V

- · Low gate charge
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- Compact industry standard SC70-6 surface mount package





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-12	V
V _{GSS}	Gate-Source Voltage		± 8	V
I _D	Drain Current - Continuous	(Note 1a)	-2	А
	- Pulsed		-6	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.75	W
		(Note 1b)	0.48	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	Note 1b)	260	°C/W		

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
.30	.30 FDG330P		8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			l		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = -250 \mu\text{A}$	-12			V
ΔBV _{DSS} ΔT, _J	Breakdown Voltage Temperature Coefficient	I_D = –250 μA, Referenced to 25°C		-2.7		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
GSSF	Gate–Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
/ _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-0.7	-1.5	V
$\Delta V_{GS(th)} = \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 μA, Referenced to 25°C		2.3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A}$ $V_{GS} = -2.5 \text{ V}, I_D = -1.7 \text{ A}$ $V_{GS} = -1.8 \text{ V}, I_D = -1.4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A}, T_1 = 125 ^{\circ}\text{C}$		84 107 145 98	110 150 215 148	mΩ
D(on)	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-6			Α
J FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_{D} = -2.0 \text{ A}$		6.8		S
Ovnamio	Characteristics			•	•	
iss	Input Capacitance	$V_{DS} = -6.0 \text{ V}, V_{GS} = 0 \text{ V},$		477		pF
oss	Output Capacitance	f = 1.0 MHz		186		pF
Prss	Reverse Transfer Capacitance			124		pF
witchin	g Characteristics (Note 2)					
d(on)	Turn-On Delay Time	$V_{DD} = -6.0 \text{ V}, I_{D} = 1 \text{ A},$		10	20	ns
	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		11	20	ns
(off)	Turn-Off Delay Time			12	22	ns
	Turn-Off Fall Time			18	32	ns
Q_g	Total Gate Charge	$V_{DS} = -6.0 \text{ V}, I_{D} = -2.0 \text{ A},$		5	7	nC
) _{gs}	Gate-Source Charge	V _{GS} = -4.5 V		0.8		nC
) _{gd}	Gate-Drain Charge	<u> </u>		1.4		nC
)rain–S	ource Diode Characteristics	and Maximum Ratings				
3	Maximum Continuous Drain-Source				-0.62	Α
SD	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -0.62 \text{ A (Note 2)}$		-0.7	-1.2	V

Notes:

- 1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
 - a.) 170°C/W when mounted on a 1 in² pad of 2 oz. copper.
 - b.) 260°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

Typical Characteristics

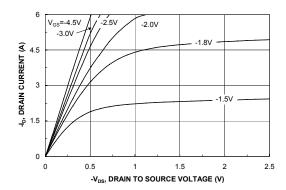


Figure 1. On-Region Characteristics.

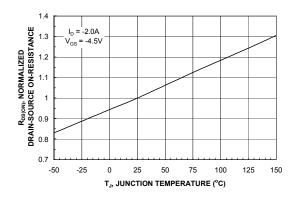


Figure 3. On-Resistance Variation with Temperature.

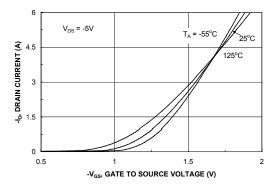


Figure 5. Transfer Characteristics.

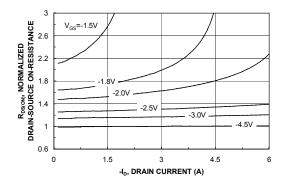


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

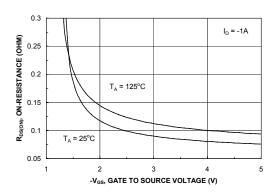


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

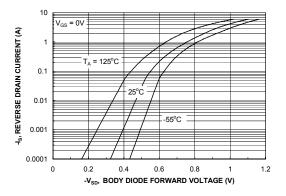
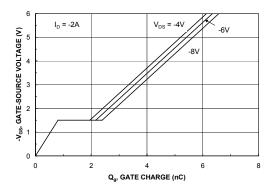


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



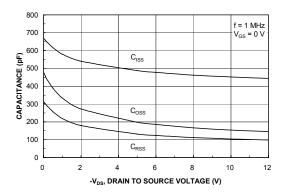


Figure 7. Gate Charge Characteristics.

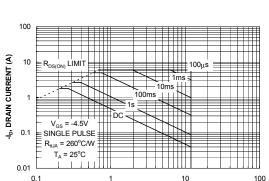


Figure 8. Capacitance Characteristics.

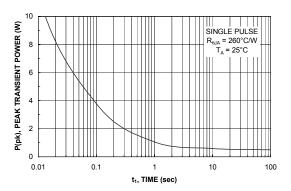


Figure 9. Maximum Safe Operating Area.

-V_{DS}, DRAIN-SOURCE VOLTAGE (V)



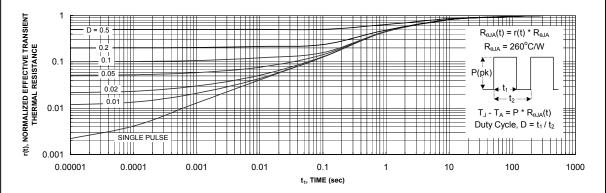


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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